

S2000AFI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

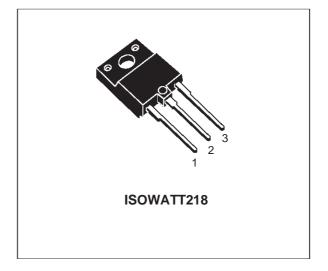
- STMicroelectronics PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- U.L. RECOGNISED ISOWATT218 PACKAGE (U.L. FILE # E81734 (N).

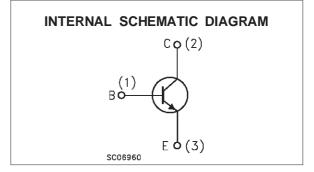
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOUR TV

DESCRIPTION

The S2000AFI is manufactured using Multiepitaxial Mesa technology for cost-effective high performance and uses a Hollow Emitter structure to enhance switching speeds.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)	1500	V
Vceo	Collector-Emitter Voltage (I _B = 0)	700	V
V _{EBO}	Emitter-Base Voltage $(I_{C} = 0)$	10	V
lc	Collector Current	8	A
I _{CM}	Collector Peak Current (t _p < 5 ms)	15	A
Ptot	Total Dissipation at $T_c = 25 \ ^{\circ}C$	50	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

December 1999

THERMAL DATA

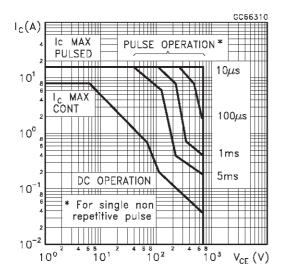
Rthj-case Thermal Resistance Junction-case	Max	2.5	°C/W	
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \,^{\circ}C$ unless otherwise specified)

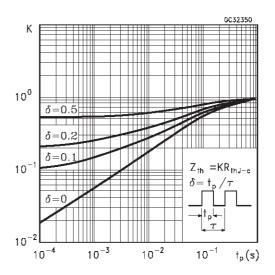
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 1500 V$ $T_{C} = 125 \ ^{o}C$ $V_{CE} = 1500 V$			1 2	mA mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	$V_{EB} = 5 V$			100	μA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage $(I_B = 0)$	I _C = 100 mA	700			V
V_{EBO}	Emitter Base Voltage (I _C = 0)	I _E = 10 mA	10			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C} = 4.5 \text{ A}$ $I_{\rm B} = 2 \text{ A}$			1	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$I_{\rm C} = 4.5 \text{ A}$ $I_{\rm B} = 2 \text{ A}$			1.3	V
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$ I_C = 4.5 \text{ A} h_{FE} = 2.5 V_{CC} = 140 \text{ V} \\ L_C = 0.9 \text{ mH} L_B = 3 \mu\text{H} $		7 0.55		μs μs
f⊤	Transition Frequency	$I_C = 0.1 \text{ A} \qquad V_{CE} = 5 \text{ V} f = 5 \text{ MHz}$		7		MHz

* Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

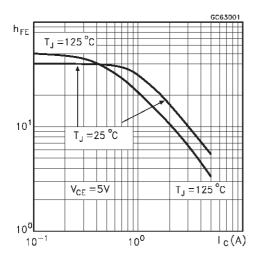
Safe Operating Area.



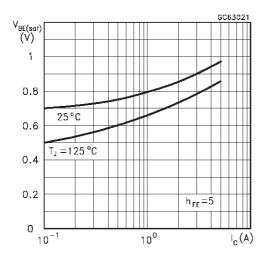
Thermal Impedance



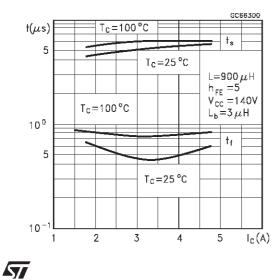
DC Current Gain



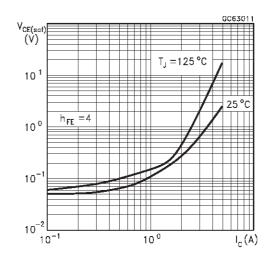
Base Emitter Saturation Voltage



Switching Time Inductive Load (see figure 1)



Collector Emitter Saturation Voltage





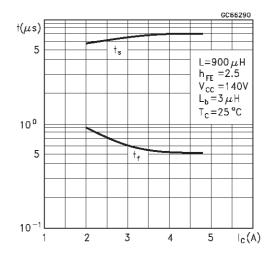
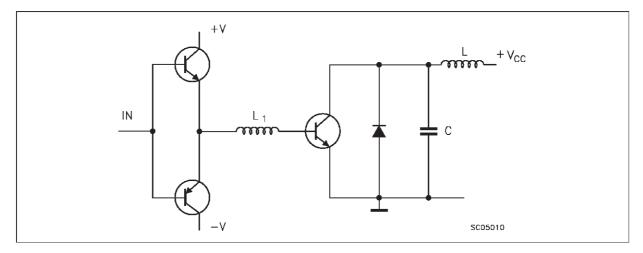
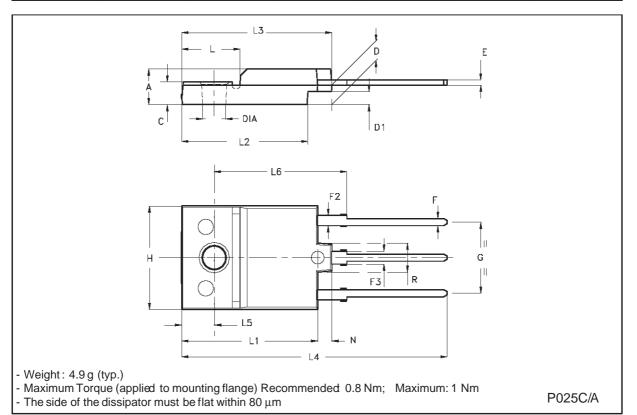


Figure 1: Inductive Load Switching Test Circuit.



DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.35		5.65	0.211		0.222
С	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
Е	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
Н	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
Ν	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146





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